# **RT3TDDM**

Composite Transistor With Resistor For Switching Application Silicon Epitaxial Type

### DESCRIPTION

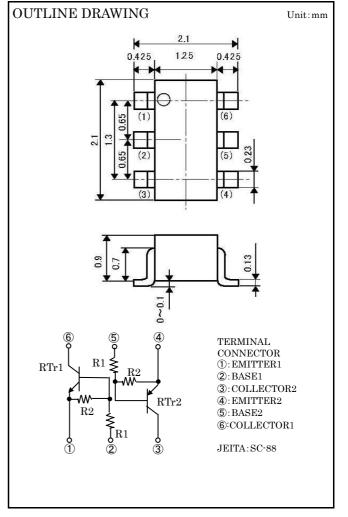
RT3TBBM is compound transistor built with RT1N237 chip and RT1P237 chip in SC-88 package.

### FEATURE

Silicon epitaxial type Each transistor elements are independent. Mini package for easy mounting

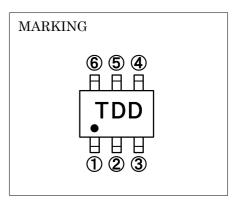
### APPLICATION

Inverted circuit, switching circuit, interface circuit, driver circuit



# MAXIMUM RATING (Ta=25°C) (RTr1\_NPN, RTr2\_PNP)

SYMBOL	PARAMETER	RATING	UNIT	
Vcbo	Collector to Base voltage	50	V	
Vebo	Emitter to Base voltage	6	V	
VCEO	Collector to Emitter voltage	50	V	
$V_{\rm IN}$	Input voltage	12	V	
IC	Collector current	100	mA	
ICM	Peak Collector current	200	mA	
PC	Collector dissipation(Total, Ta=25°C)	150	mW	
Tj	Junction temperature	+150	°C	
$\mathrm{T}_{\mathrm{stg}}$	Storage temperature	-55~+150	°C	



₩PNP built in transistor of "-"sign is abbreviation.

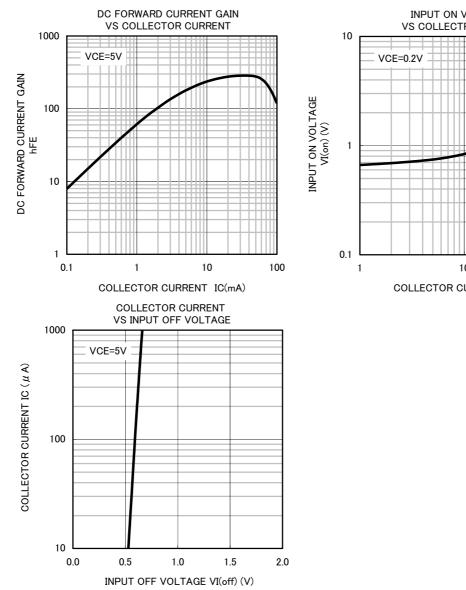
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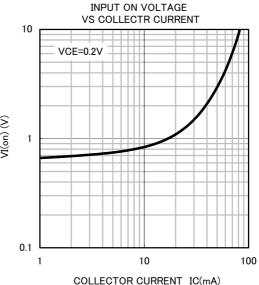
# ELECTRICAL CHARACTERISTICS (Ta=25°C) (RTr1\_NPN, RTr2\_PNP)

Symbol	Parameter		Limits				
		Test conditions		MAX	TYP	MIN	Unit
V(BR)CEO	Collector to Emitter break down voltage	I с=100µА, R <sub>BE</sub> =∞		50	—	-	V
Ісво	Collector cut off current	at off current $V_{CB}$ =50V, I $_{E}$ =0mA		-	—	0.1	μA
hFE	DC forward current gain	V <sub>CE</sub> =5V, I C=10mA		80	—	—	-
VCE(sat)	Collector to Emitter saturation voltage	I <sub>c</sub> =10mA, I <sub>B</sub> =0. 5mA		-	—	0.3	V
VI(ON)	Input on voltage	$V_{CE}$ =0.2V, I c=5mA		-	0.7	1.1	V
VI(OFF)	Input off voltage	V <sub>CE</sub> =5V, I c=100µA		0.5	0.6	—	V
R1	Input resistor	-		1.5	2.2	2.9	KΩ
$R_2/R_1$	Resistor ratio	-		-	22	—	—
fT	Gain band width product	V <sub>CE</sub> =6V, I <sub>E</sub> =10mA	RTr1	—	200	—	MHz
			RTr2	_	150	_	

PNP built in transistor of "-"sign is abbreviation.

# TYPICAL CHARACTERISTICS (RTr1\_NPN)

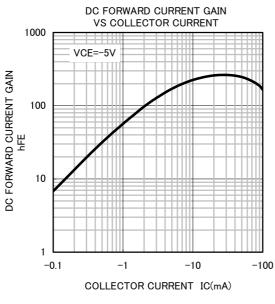


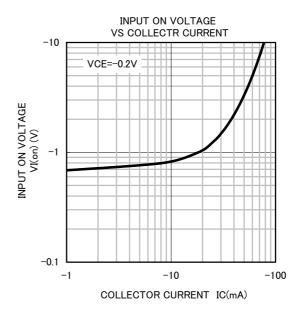


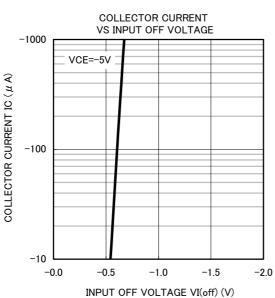
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## TYPICAL CHARACTERISTICS (RTr2\_PNP)









6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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